



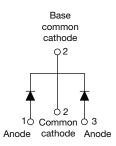
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Vishay Semiconductors

# HEXFRED®, Ultrafast Soft Recovery Diode, 2 x 4 A



**TO-220AB** 



PRODUCT SUMMARY						
Package	TO-220AB					
I <sub>F(AV)</sub>	2 x 4 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.4 V					
t <sub>rr</sub> typ.	17 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Common cathode					

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current per leg	⊢ I <sub>F</sub>	T <sub>C</sub> = 100 °C	4	۸		
per device			8			
Single pulse forward current	I <sub>FSM</sub>		25	А		
Maximum repetitive forward current	I <sub>FRM</sub>		16			
Maniana	_	T <sub>C</sub> = 25 °C	25	14/		
Maximum power dissipation	$P_{D}$	T <sub>C</sub> = 100 °C	10	W		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		



## VS-HFA08TA60CPbF, VS-HFA08TA60C-N3

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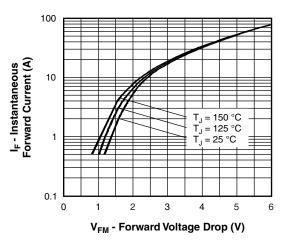
<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		600	-	-	
Maximum forward voltage		I <sub>F</sub> = 4.0 A	See fig. 1	-	1.5	1.8	V
	$V_{FM}$	I <sub>F</sub> = 8.0 A		-	1.8	2.2	
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7	
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	Coo fig. 0	-	0.17	3.0	_
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	44	300	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	17	-		
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42	ns	
ooo ng. o, o ana ro	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 4.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	38	57		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A nC	
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60		
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105	IIC	
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 11 and 12	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	- A/µs	
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	- Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB	HFA08TA60C				



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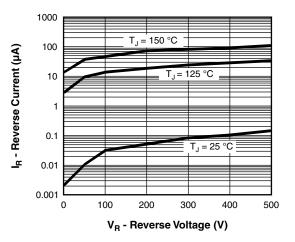


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

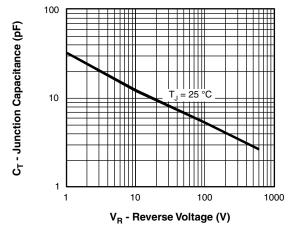


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

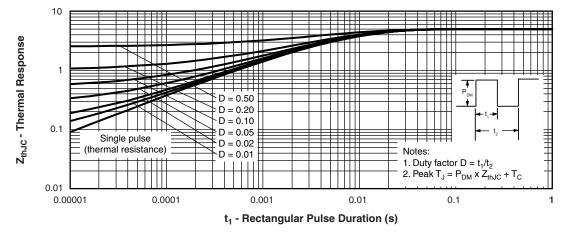


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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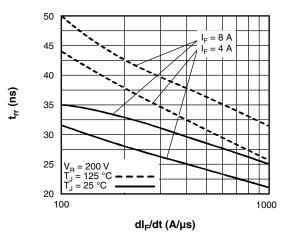


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>E</sub>/dt

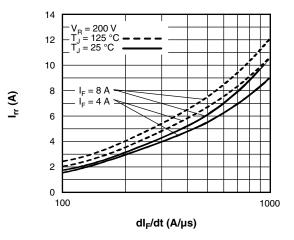


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

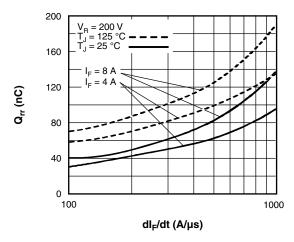


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

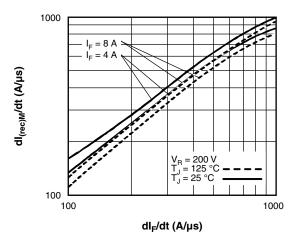
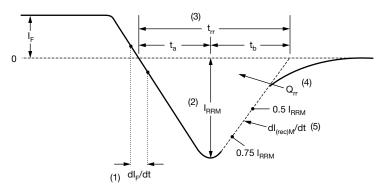


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{F}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\rm Q_{rr}$  area under curve defined by  $\rm t_{rr}$  and  $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

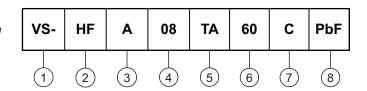
Fig. 9 - Reverse Recovery Waveform and Definitions

## VS-HFA08TA60CPbF, VS-HFA08TA60C-N3

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

- Current rating (08 = 8 A)

5 - Package:

TA = TO-220AB

Voltage rating (60 = 600 V)

7 - Circuit configuration:

C = common cathode

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08TA60CPbF	50	1000	Antistatic plastic tube				
VS-HFA08TA60C-N3	50	1000	Antistatic plastic tube				

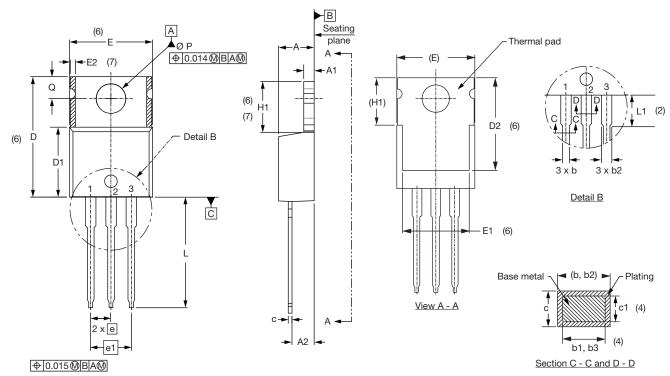
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95222			
Part marking information	TO-220ABPbF	www.vishay.com/doc?95225			
Fait marking information	TO-220AB-N3	www.vishay.com/doc?95028			



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## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



# Lead tip

## Lead assignments

### <u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS		INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INC	INCHES		
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Е	10.11	10.51	0.398	0.414	3, 6	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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